Device Modeling Report

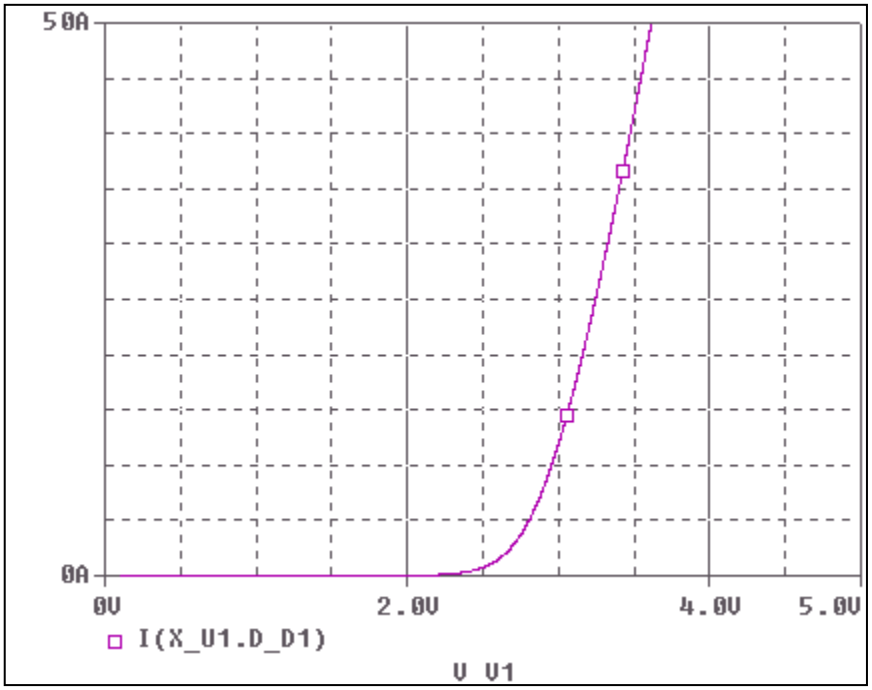
COMPONENTS: Light-Emitting Diode (LED) Professional
PART NUMBER: OSWT5111A
MANUFACTURER: OPTO SUPPLY
REMARK: 60 degree C

Bee Technologies Inc.

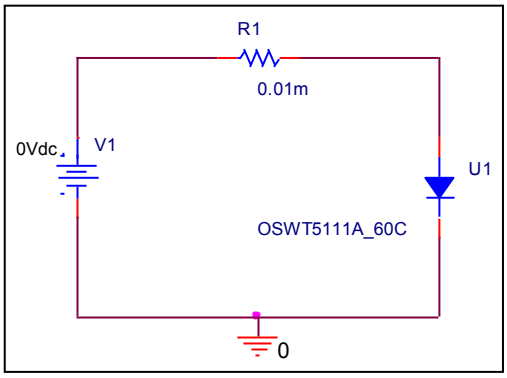
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

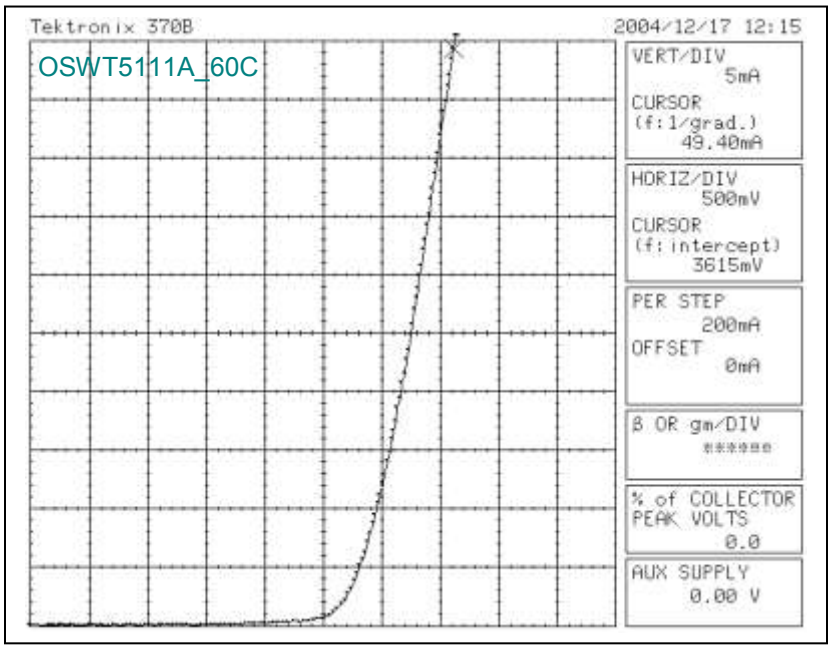
Circuit Simulation Result



Evaluation Circuit

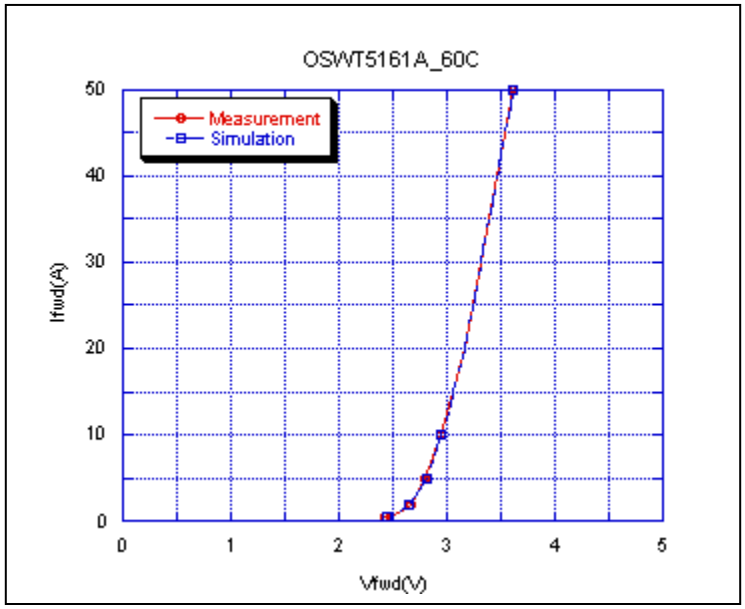


Forward Current Characteristic Reference



Comparison Graph

Circuit Simulation Result

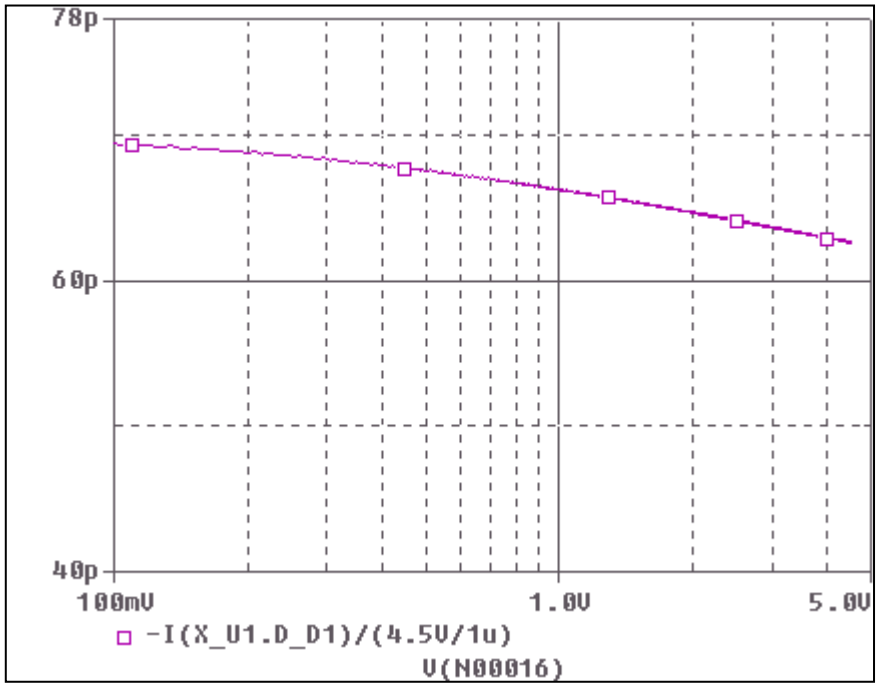


Simulation Result

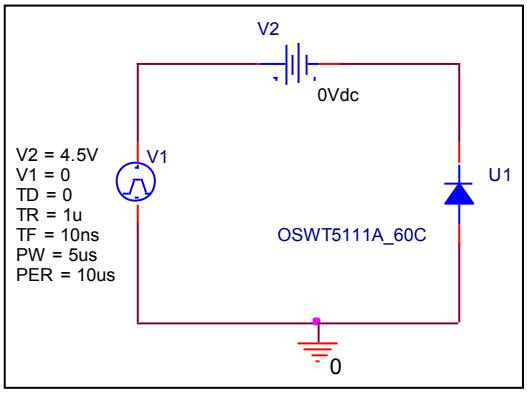
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.5	2.42	2.441	0.8677
1	2.56	2.541	0.7421
2	2.665	2.646	0.7129
5	2.795	2.817	0.7871
10	2.945	2.954	0.3056
20	3.16	3.159	0.0316
50	3.615	3.614	0.0276

Capacitance Characteristic

Circuit Simulation Result

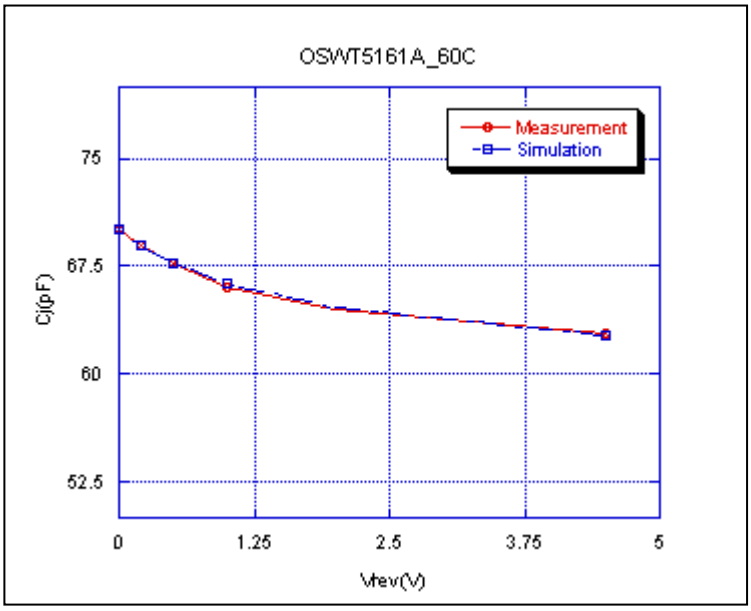


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

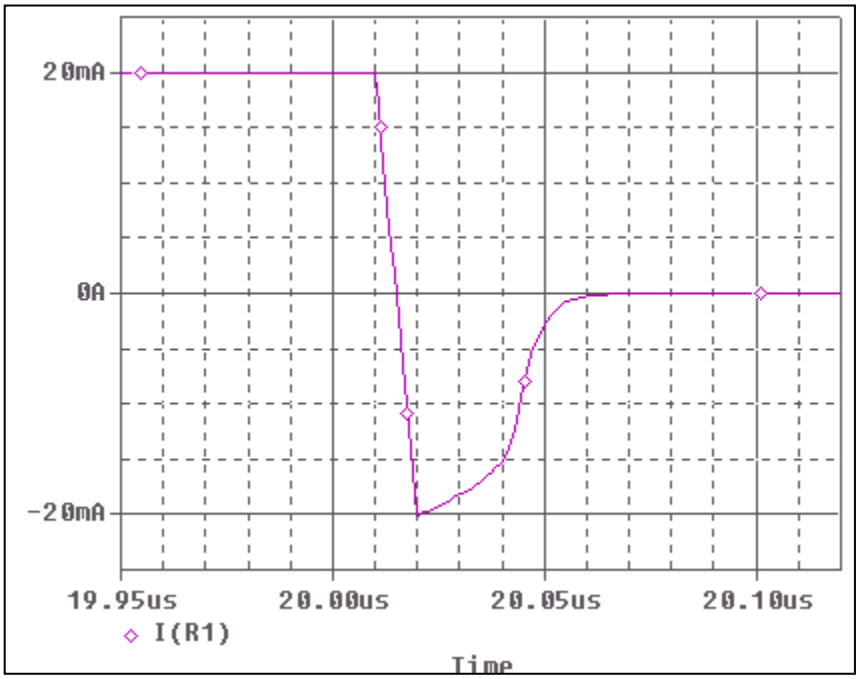


Simulation Result

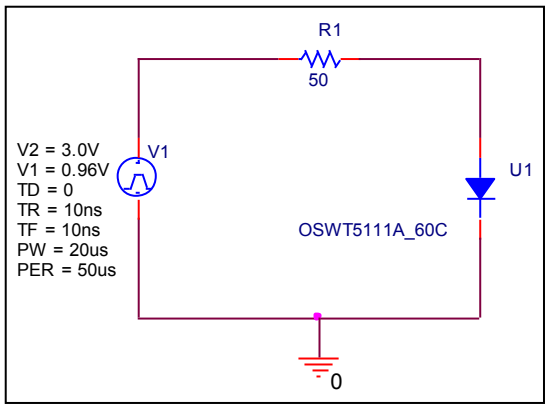
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	70.06	70.06	0
0.1	69.465	69.371	0.13531
0.2	68.91	68.883	0.03918
0.5	67.65	67.651	0.00147
1	66.1	66.285	0.27987
2	64.48	64.64	0.24813
4.5	62.85	62.692	0.25139

Reverse Recovery Characteristic

Circuit Simulation Result



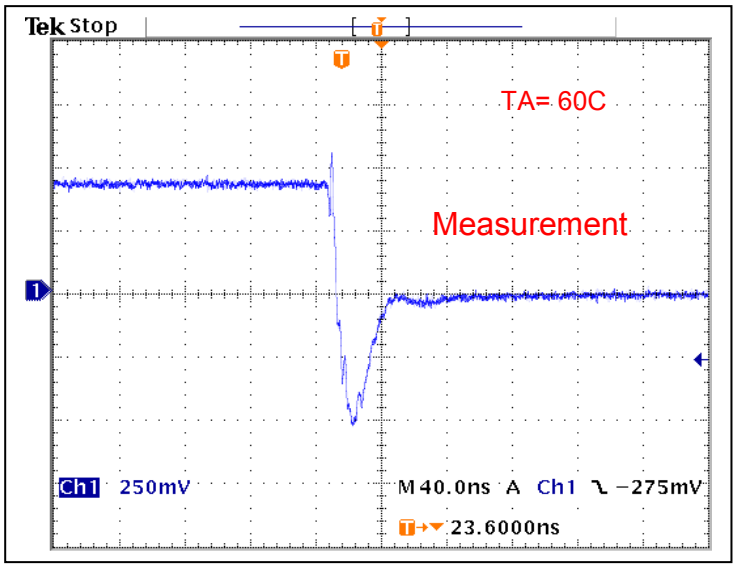
Evaluation Circuit



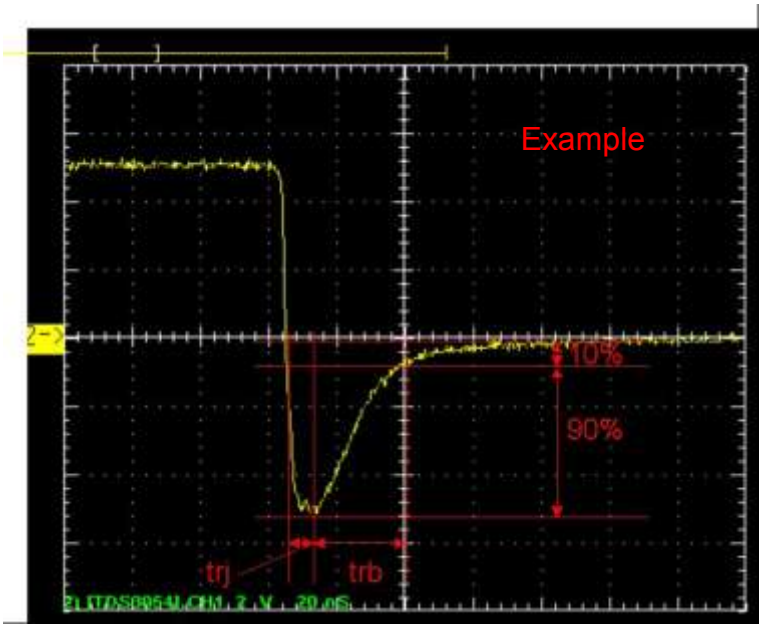
Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
trj	12.4	ns	12.36	ns	0.32258
trb	23.6	ns	23.61	ns	0.04237

Reverse Recovery Characteristic Reference



Trj =12.4(ns)
Trb=23.6(ns)
Conditions: Ifwd=Irev=0.02(A), Rl=50



Relation between trj and trb